

MMDT3906

MMDT3906 SOT-363 Plastic-Encapsulate Transistors

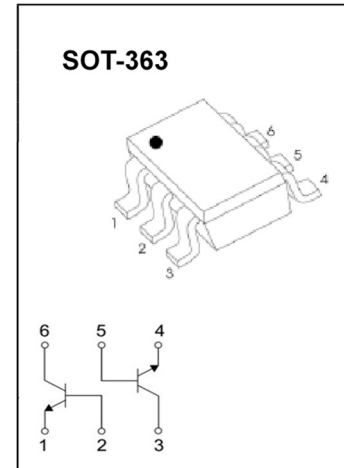
General description

SOT-363 Plastic-Encapsulate Transistors

FEATURES

- DUAL TRANSISTOR (PNP+PNP)
- Complementary to MMDT3904
- Ideal for low power amplification and switching

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-40	V
V _{CE0}	Collector-Emitter Voltage	-40	V
V _{EB0}	Emitter-Base Voltage	-5	V
I _c	Collector Current -Continuous	-200	A
P _c	Collector Power Dissipation	200	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-+150	°C

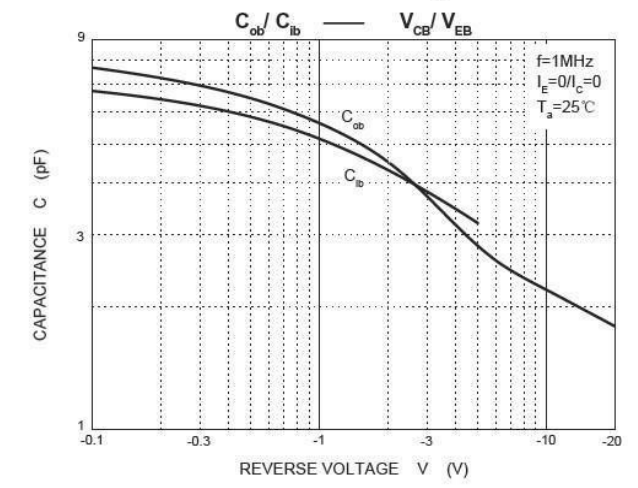
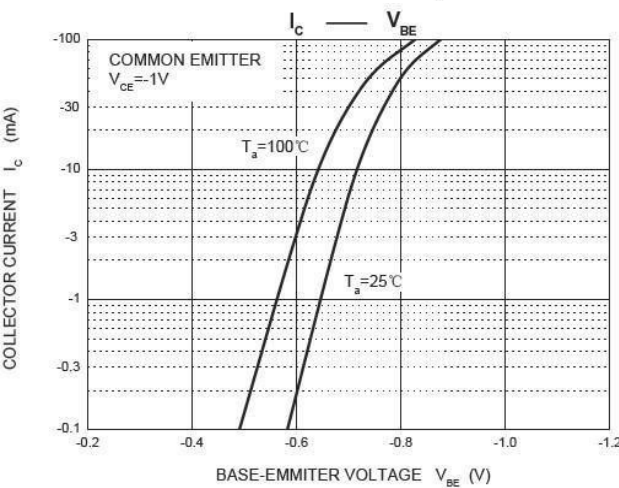
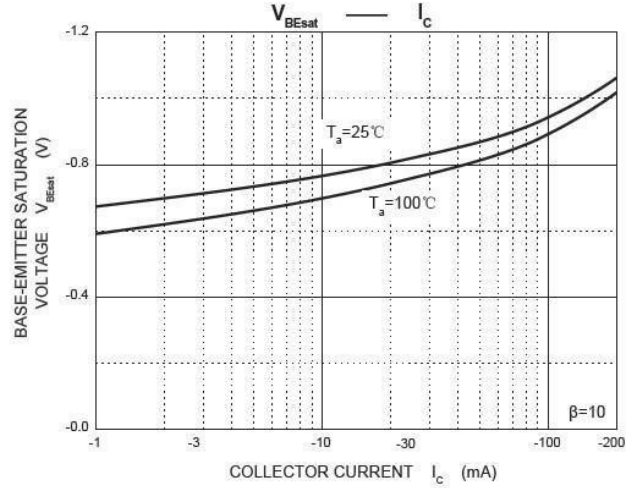
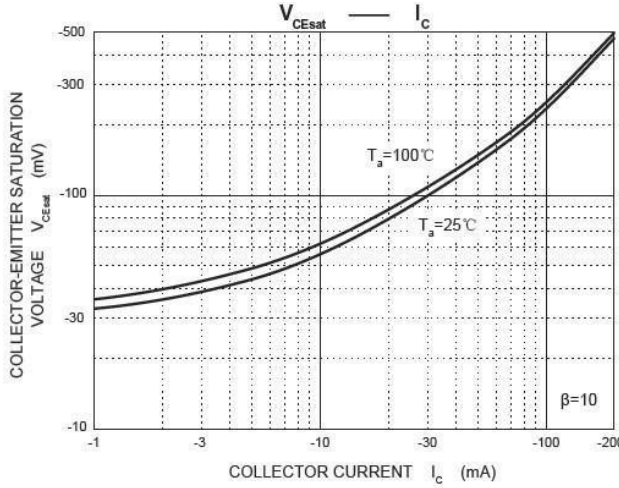
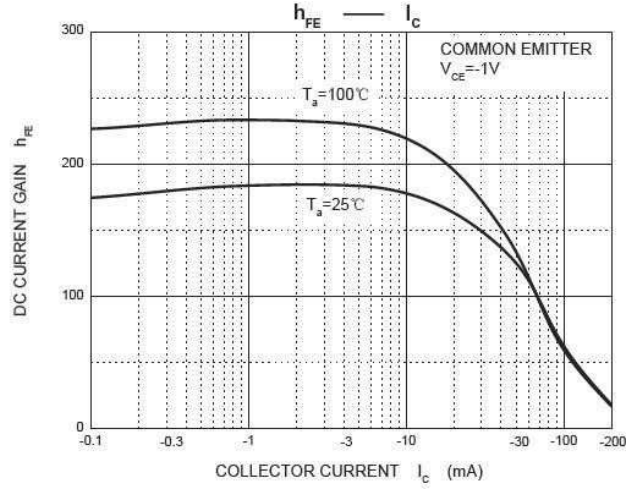
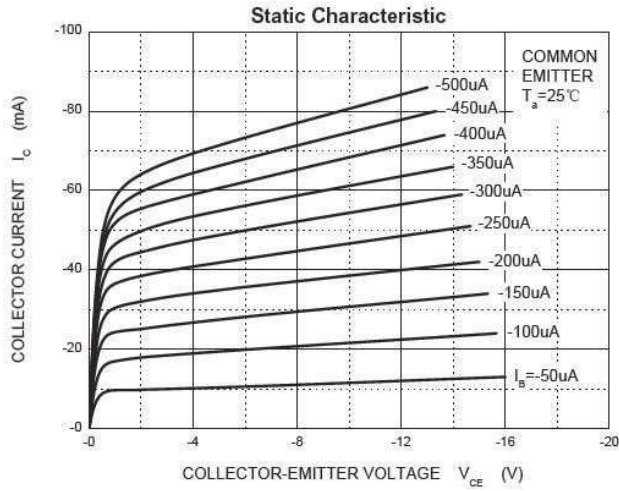


MARKING : K3N

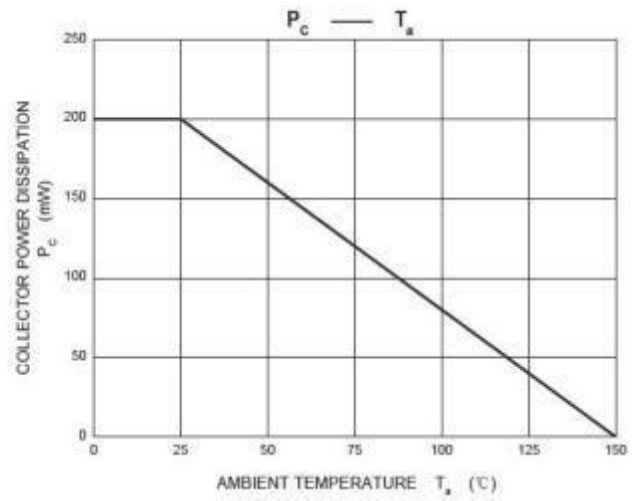
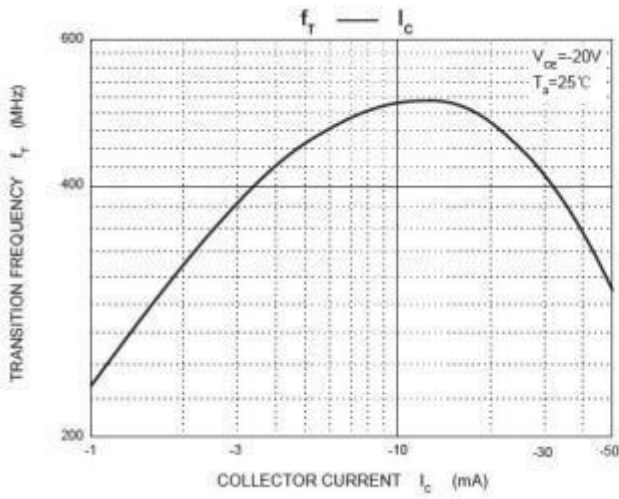
Absolute Maximum Ratings(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	I _C =10μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V(BR)CEO	I _C =1mA, I _B =0	-40			V
Emitter-base breakdown voltage	V(BR)EBO	I _E =10μA, I _C =0	-5			V
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-50	nA
Collector cut-off current	I _{CEX}	V _{CE} =-30V, V _{BE(off)} =-3V			-50	nA
DC current gain	hFE(1)	V _{CE} =-1V, I _C =-0.1mA	60			
	hFE(2)	V _{CE} =-1V, I _C =-1mA	80			
	hFE(3)	V _{CE} =-1V, I _C =-10mA	100		300	
	hFE(4)	V _{CE} =-1V, I _C =-50mA	60			
	hFE(5)	V _{CE} =-1V, I _C =-100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =-10mA, I _B =-1mA			-0.25	V
	V _{CE(sat)2}	I _C =-50mA, I _B =-5mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C =-10mA, I _B =-1mA	-0.65		-0.85	V
	V _{BE(sat)2}	I _C =-50mA, I _B =-5mA			-0.95	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f=100MHz	250			MHz
Delay time	t _d	V _{CC} =3V, V _{BE(off)} =-0.5V			35	nS
Rise time	t _r	I _C =10mA, I _{B1} =-I _{B2} =1mA			35	nS
Storage time	t _s	V _{CC} =3V, I _C =10mA			225	nS
Fall time	t _f	I _{B1} =-I _{B2} =1mA			75	nS

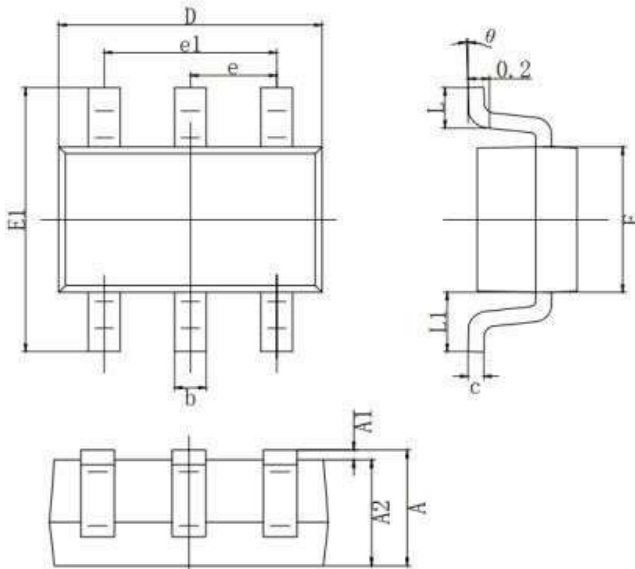
MMDT3906 Typical characteristics



MMDT3906



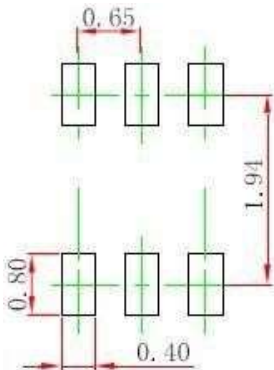
SOT-363 PACKAGE OUTLINE Plastic surface mounted package



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
e	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
theta	0°	8°

Precautions: PCB Design

Recommended land dimensions for SOT-363. Electrode patterns for PCBs



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

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